DESCRIPTION:

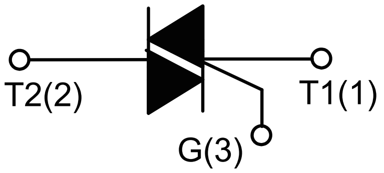
The BT136S-800E SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.

TO-263

TO-252

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	600/800	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	℃
Operating junction temperature range		T_j	-40-125	℃
Repetitive peak off-state voltage(T_j=25℃)		V_{DRM}	600/800	V
Repetitive peak reverse voltage(T_j=25℃)		V_{RRM}	600/800	V
RMS on-state current	TO-252 (T_C=100℃)	$I_{T(RMS)}$	4	A
	TO-263 (T_C=95℃)			
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	35	A
I^2t value for fusing (tp=10ms)		I^2t	6.1	A^2s
Critical rate of rise of on-state current (I_G=2×I_{GT})	Ⅰ-Ⅱ-Ⅲ	dI/dt	50	A/μs
	Ⅳ		10	
Peak gate current		I_{GM}	2	A
Average gate power dissipation		$P_{G(AV)}$	0.5	W
Peak gate power		P_{GM}	5	W

ELECTRICAL CHARACTERISTICS (Tj=25℃ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				T	D	E	F	
I_{GT}	V_D=12V	Ⅰ-Ⅱ-Ⅲ	MAX	5	5	10	25	mA
		Ⅳ		5	10	25	70	
V_{GT}		ALL	MAX	1.3				V
V_{GD}	V_D=V_{DRM} T_j=125℃ R_L=3.3KΩ	ALL	MIN	0.2				V
I_L	I_G=1.2I_{GT}	Ⅰ-Ⅲ	MAX	10	20	30	40	mA
		Ⅱ-Ⅳ		15	35	45	60	
I_H	I_T=100mA		MAX	5	15	25	30	mA
dV/dt	V_D=2/3V_{DRM} Gate Open T_j=125℃		MIN	20	50	100	150	V/μs
(dV/dt)c	(dI/dt)c=1.7A/ms T_j=125℃		MIN	0.1	0.1	0.5	5	V/μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I_{TM}=5.5A tp=380μs	T_j=25℃	1.6	V
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25℃	5	μA
I_{RRM}		T_j=125℃	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-252 2.8		℃/W
		TO-263	3.8	
$R_{th(j-a)}$	junction to ambient	TO-252 70		℃/W
		TO-263	45	

FIG.1: Maximum power dissipation versus RMS on-state current

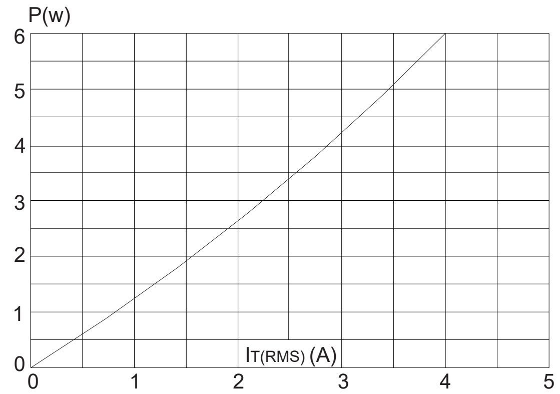


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35μm)

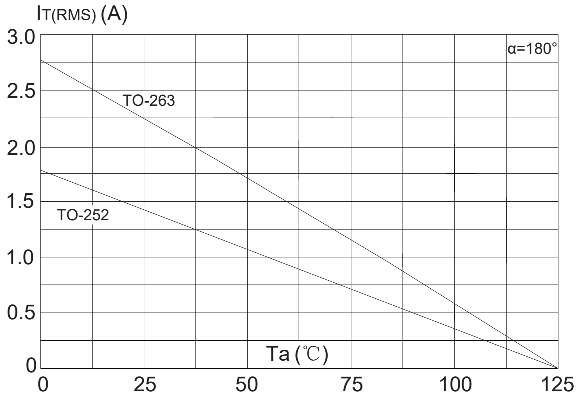


FIG.3: Surge peak on-state current versus number of cycles

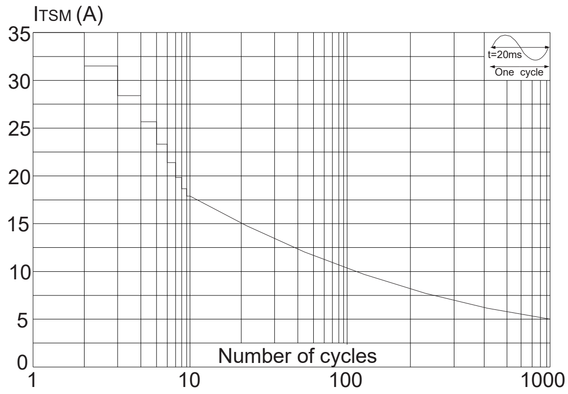


FIG.4: On-state characteristics (maximum values)

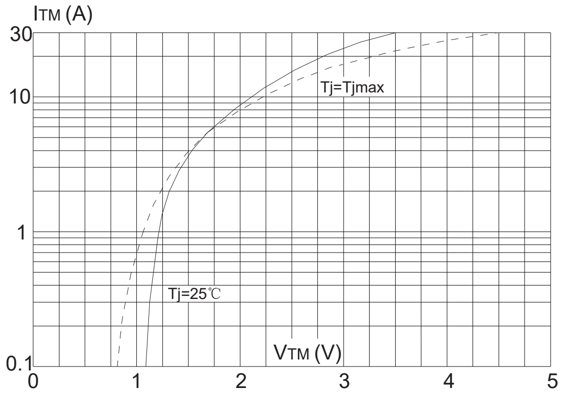


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms and corresponding value of I^2t (Ⅰ-Ⅱ-Ⅲ:dI/dt < 50A/μs; Ⅳ:dI/dt < 10A/μs)

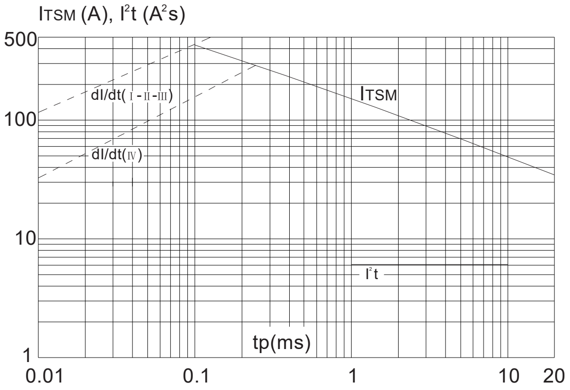


FIG.6: Relative variations of gate trigger current versus junction temperature

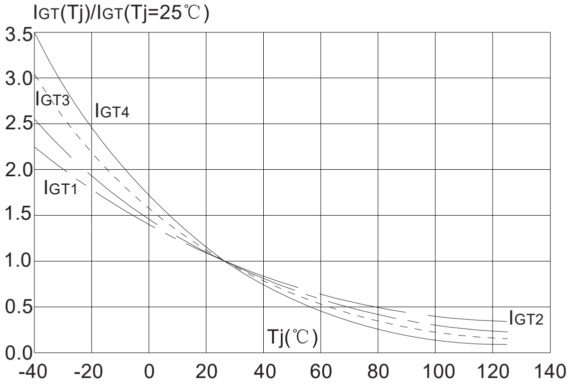


FIG.7: Relative variations of holding current versus junction temperature

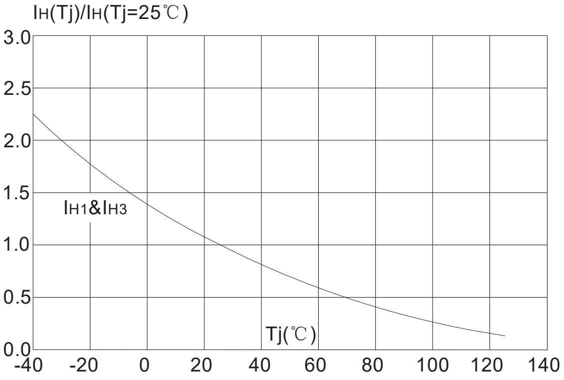
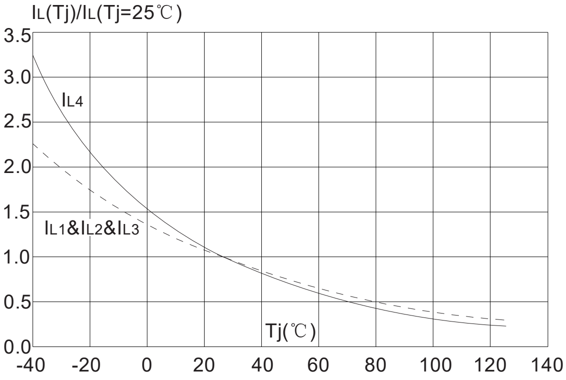


FIG.8: Relative variations of latching current versus junction temperature



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L)to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃